

isc Silicon NPN Power Transistor

2SC4744

DESCRIPTION

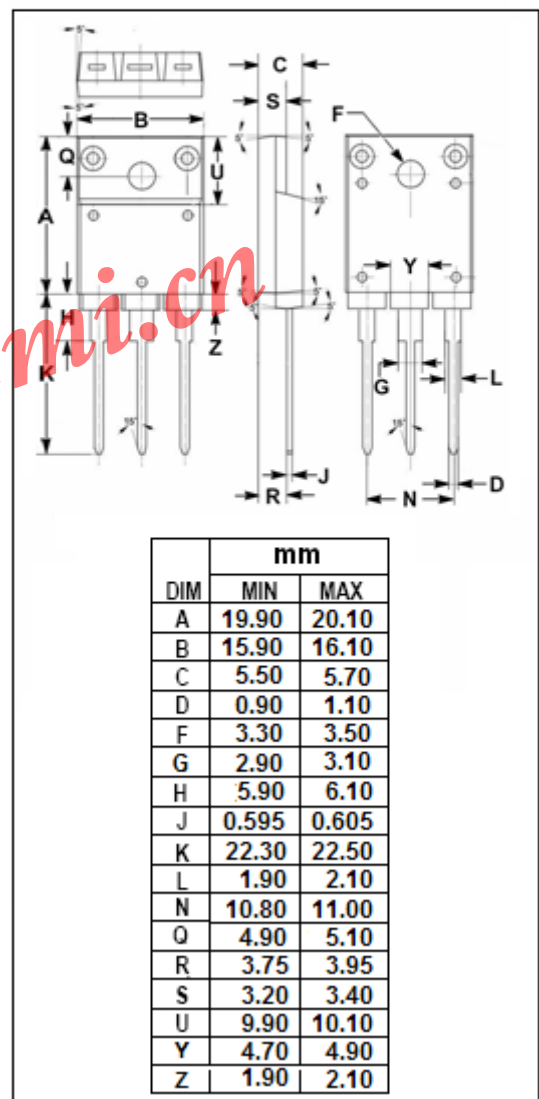
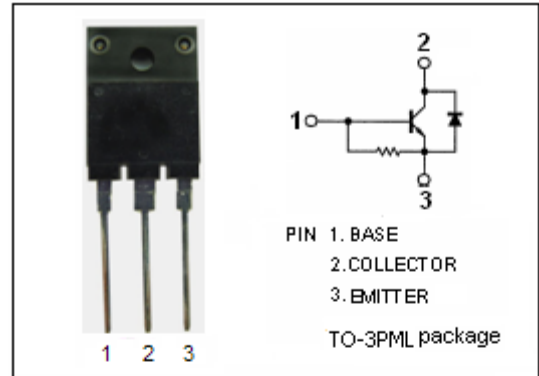
- High Breakdown Voltage-
: $V_{CBO}= 1500V$ (Min)
- High Switching Speed
- Built-in Damper Diode

APPLICATIONS

- Designed for character display horizontal deflection output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
$I_{C(peak)}$	Collector Current-Peak	7	A
$I_{C(surge)}$	Collector Current-Surge	16	A
I_D	C-E Diode Forward Current	7	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=400\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=1.25\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=1.25\text{A}$			1.5	V
I_{CES}	Collector Cutoff Current	$V_{CE}=1500\text{V}; R_{BE}=0$			500	μA
h_{FE}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$			25	
V_{ECF}	C-E Diode Forward Voltage	$I_F=6\text{A}$			2.0	V
t_f	Fall Time	$I_{CP}=5\text{A}; I_{B1}=1\text{A}; I_{B2}=-2\text{A}$			0.4	μs

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